

● **General Description**

The TF050N04N uses advanced trench technology and design to provide excellent RDS(ON) with low gate charge. It can be used in a wide variety of applications.

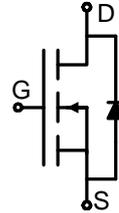
● **Features**

- Advance device constructure
- Low R_{DS(ON)} to minimize conduction loss
- Low Gate Charge for fast switching
- Low Thermal resistance

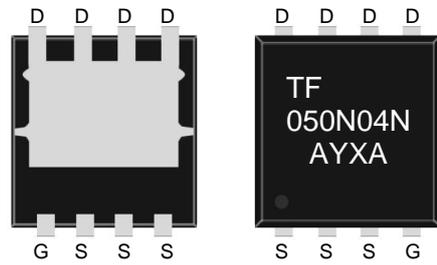
● **Application**

- Synchronous Rectification for AC-DC/DC-DC converter
- Power Tools

● **Product Summary**



$V_{DS} = 40V$ $I_D = 80A$
 $R_{DS(ON)(10V\ typ)} = 4.1m\Omega$
 $R_{DS(ON)(4.5V\ typ)} = 5.2m\Omega$



PDFNWB5x6-8L

● **Package Marking and Ordering Information:**

Part NO.	TF050N04N
Marking1	TF050N04N
Marking2	TF:tuofeng; AA:device code; Y:year code; X:Week
Basic ordering unit	5000 / PCS

● **Absolute Maximum Ratings** (T_C = 25°C)

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V _{DS}	40	V
Gate-Source Voltage	V _{GS}	±20	V
Continuous Drain Current	I _{D@TC=25°C}	80	A
	I _{D@TC=75°C}	56	A
	I _{D@TC=100°C}	48	A
Pulsed Drain Current ①	I _{DM}	180	A
Total Power Dissipation	P _{D@TC=25°C}	45	W
Total Power Dissipation	P _{D@TA=25°C}	2.0	W
Operating Junction Temperature	T _J	-55 to 150	°C
Storage Temperature	T _{STG}	-55 to 150	°C
Single Pulse Avalanche Energy	E _{AS}	105	mJ



●Thermal resistance

Parameter	Symbol	Min.	Typ.	Max.	Unit
Thermal resistance, junction - case	R _{thJC}	-	-	6.5	° C/W
Thermal resistance, junction - ambient	R _{thJA}	-	-	50	° C/W
Soldering temperature, wavesoldering for 8 s	T _{sold}	-	-	265	° C

●Electronic Characteristics

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _D =250uA	40	-	-	V
Gate Threshold Voltage	V _{GS(TH)}	V _{GS} =V _{DS} , I _D =250uA	1.1	1.5	2.1	V
Drain-Source Leakage Current	I _{DSS}	V _{DS} =40 V _{GS} =0V	-	-	1.0	uA
Gate- Source Leakage Current	I _{GSS}	V _{GS} =±20V ,V _{DS} =0V	-	-	±100	nA
Static Drain-source On Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =30A	-	4.1	5.5	mΩ
		V _{GS} =4.5V, I _D =20A	-	5.2	6.5	mΩ
Forward Transconductance	g _{FS}	V _{DS} =25V, I _D =20A	-	12	-	S
Source-drain voltage	V _{SD}	I _S =20A	-	-	1.2	V

●Electronic Characteristics

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Input capacitance	C _{iss}	f = 1MHz V _{DS} =20V V _{GS} = 0V	-	2174	-	pF
Output capacitance	C _{oss}		-	146.3	-	
Reverse transfer capacitance	C _{rss}		-	150.5	-	

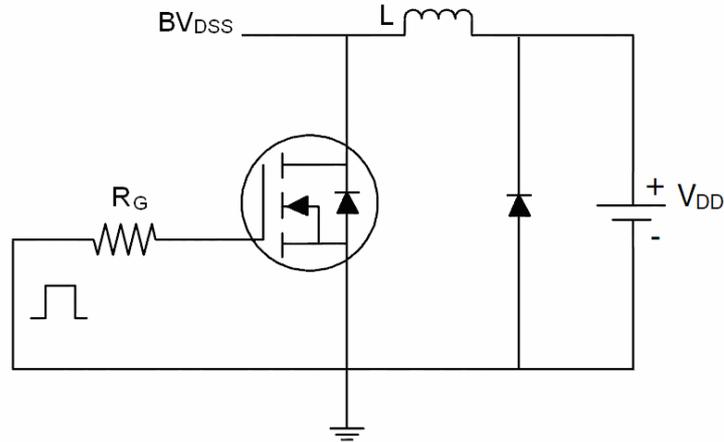
●Gate Charge characteristics(T_a = 25°C)

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Total gate charge	Q _g	V _{DD} = 20V	-	43.28	-	nC
Gate - Source charge	Q _{gs}	I _D = 30A	-	23.93	-	
Gate - Drain charge	Q _{gd}	V _{GS} = 10V	-	15.22	-	

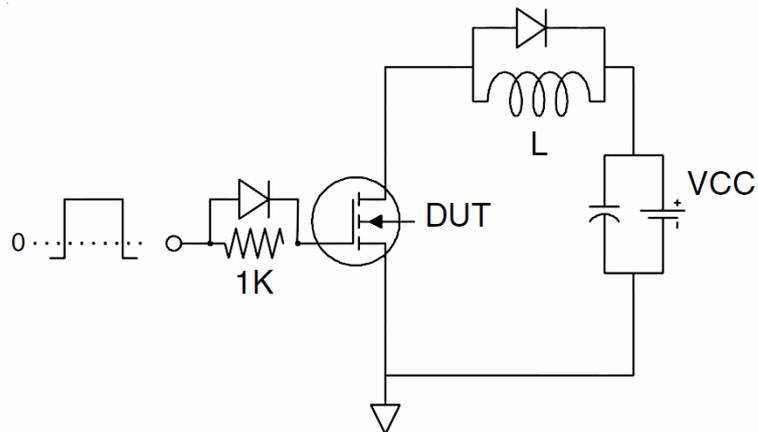
Note: ① Pulse Test : Pulse width ≤ 300μs, Duty cycle ≤ 2% ;

Test Circuit

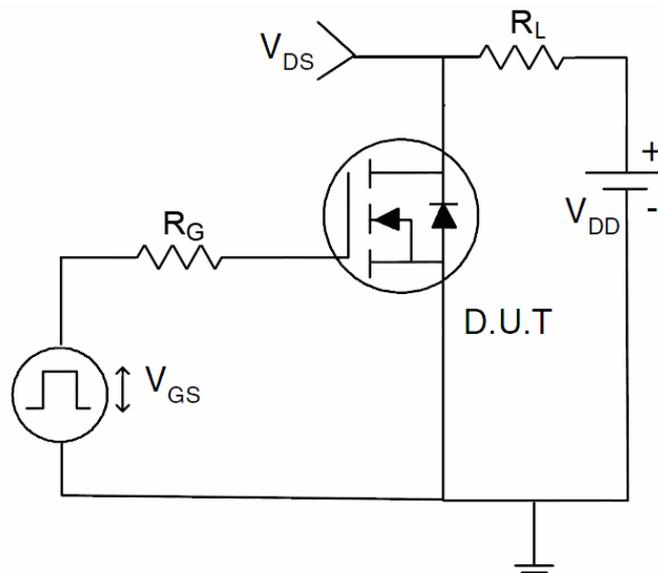
1) E_{AS} test Circuit



2) Gate charge test Circuit



3) Switch Time Test Circuit



Typical Electrical and Thermal Characteristics

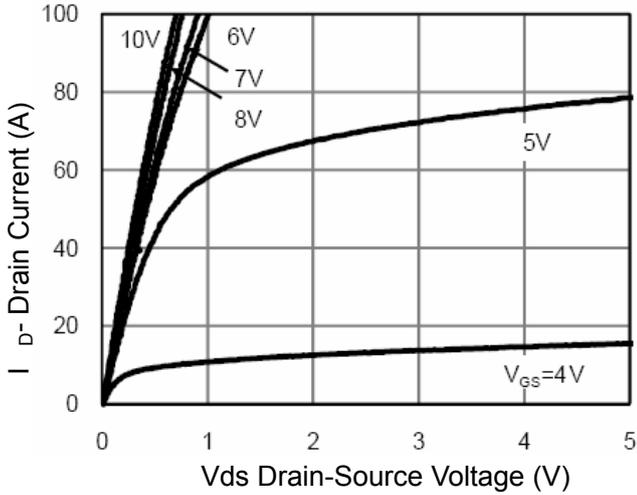


Figure 1 Output Characteristics

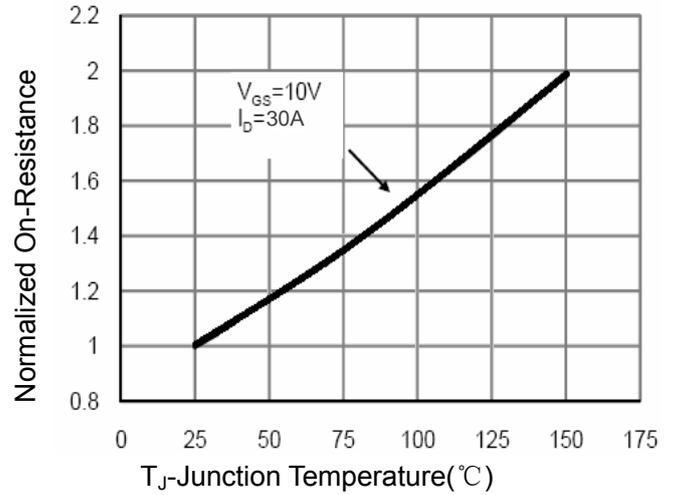


Figure 4 Rdson-Junction Temperature

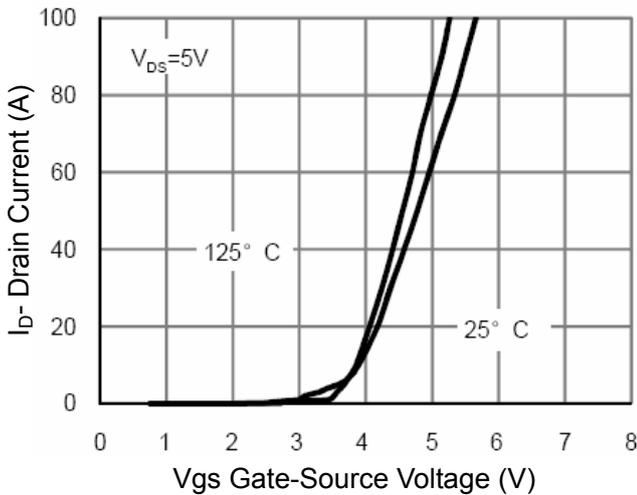


Figure 2 Transfer Characteristics

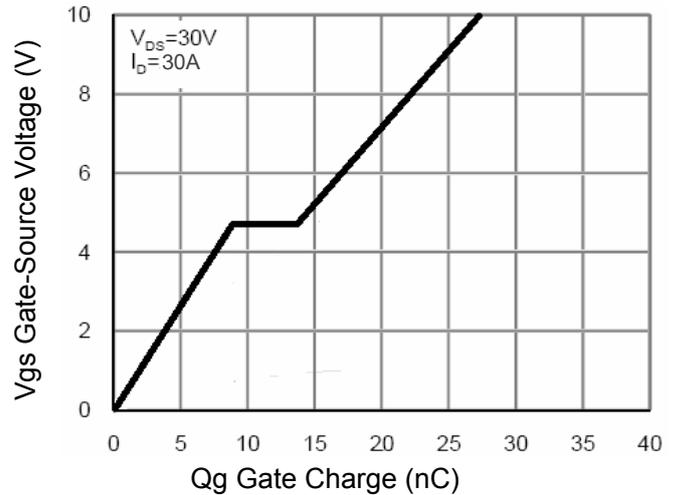


Figure 5 Gate Charge

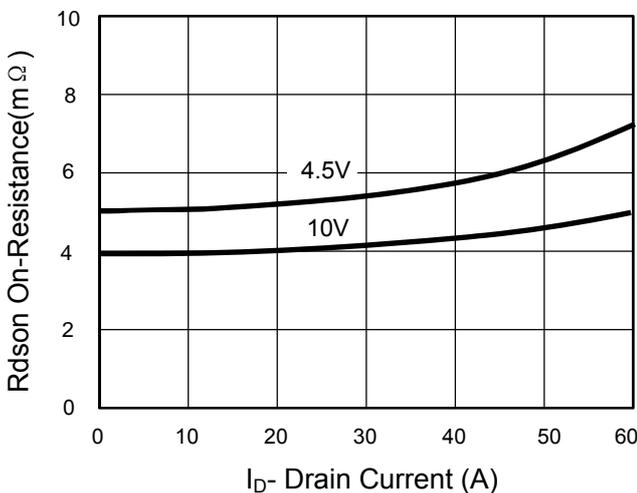


Figure 3 Rdson- Drain Current

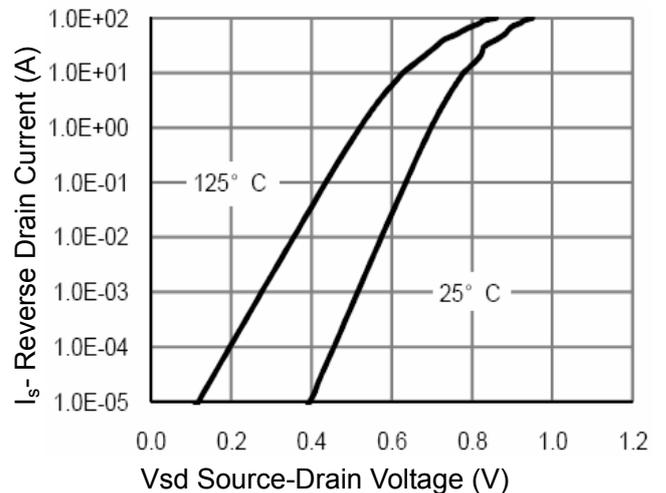


Figure 6 Source- Drain Diode Forward

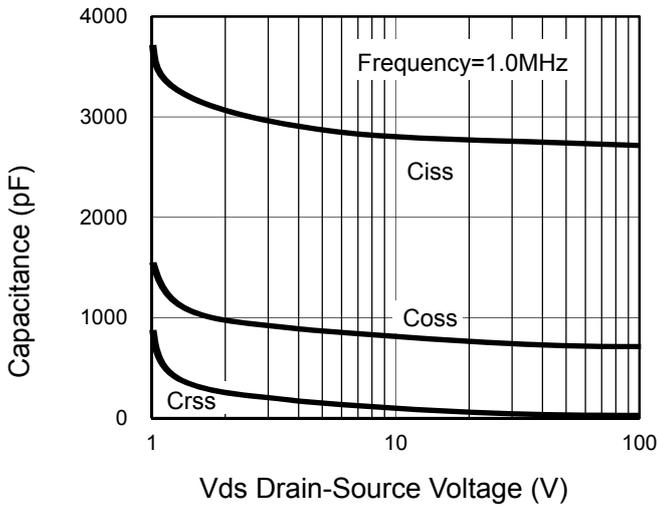


Figure 7 Capacitance vs Vds

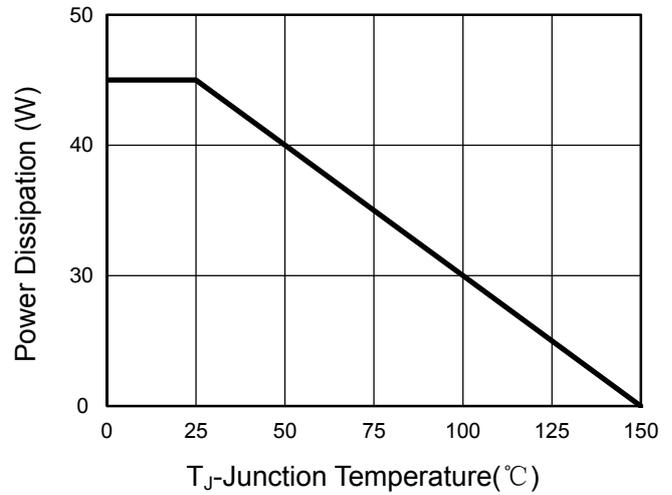


Figure 9 Power De-rating

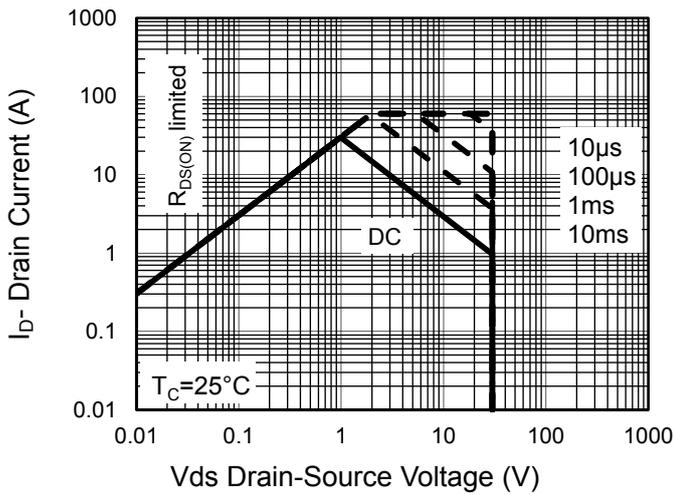


Figure 8 Safe Operation Area

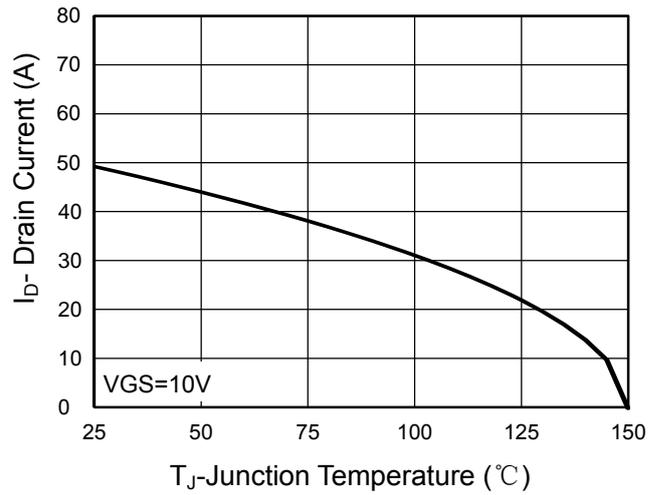


Figure 10 Current De-rating

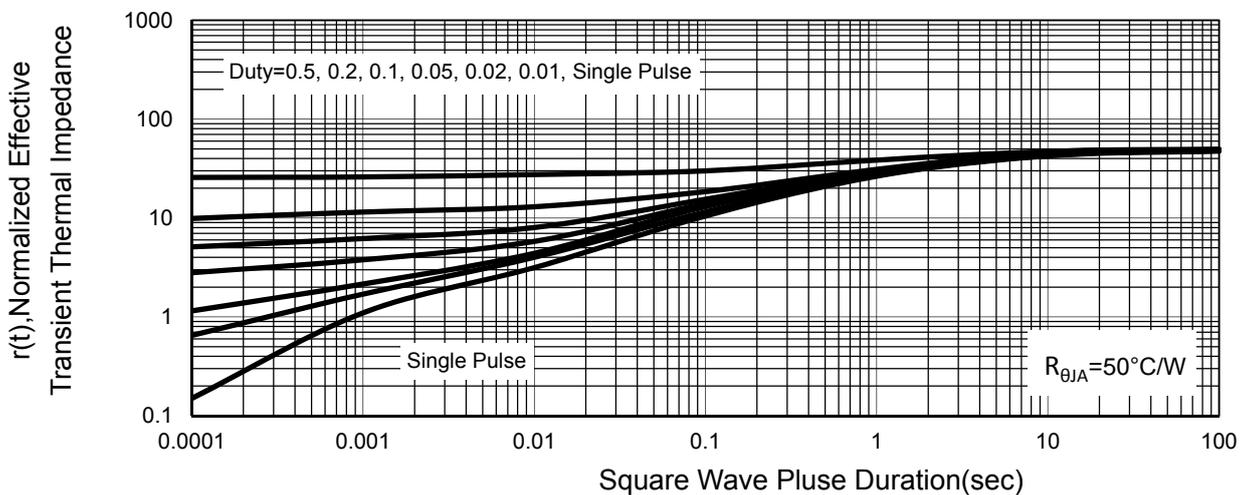
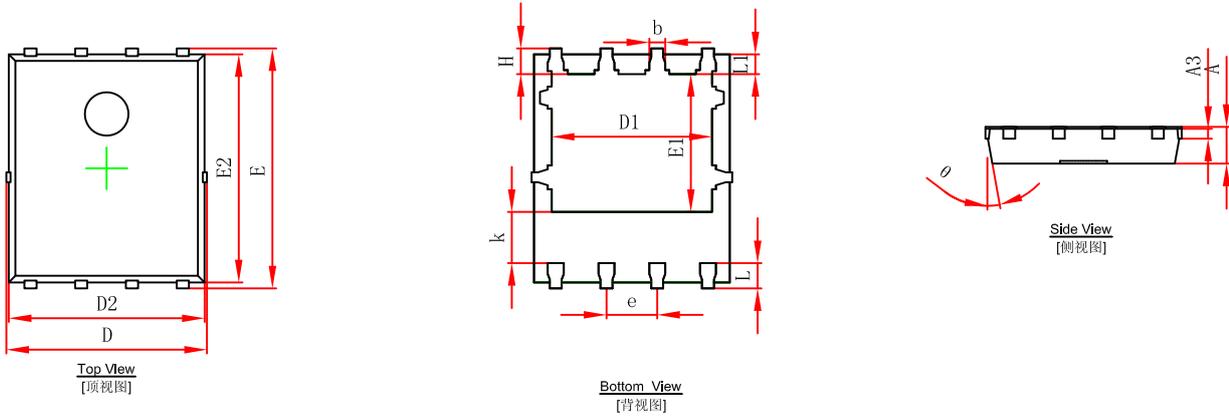


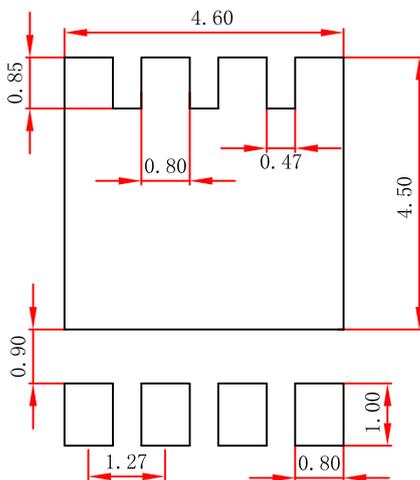
Figure 11 Normalized Maximum Transient Thermal Impedance

PDFNWB5x6-8L Package Outline Dimensions



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.900	1.000	0.035	0.039
A3	0.254REF.		0.010REF.	
D	4.944	5.096	0.195	0.201
E	5.974	6.126	0.235	0.241
D1	3.910	4.110	0.154	0.162
E1	3.375	3.575	0.133	0.141
D2	4.824	4.976	0.190	0.196
E2	5.674	5.826	0.223	0.229
k	1.190	1.390	0.047	0.055
b	0.350	0.450	0.014	0.018
e	1.270TYP.		0.050TYP.	
L	0.559	0.711	0.022	0.028
L1	0.424	0.576	0.017	0.023
H	0.574	0.726	0.023	0.029
θ	10°	12°	10°	12°

PDFNWB5x6-8L Suggested Pad Layout



- Note:
1. Controlling dimension: in millimeters.
 2. General tolerance: $\pm 0.05\text{mm}$.
 3. The pad layout is for reference purposes only.